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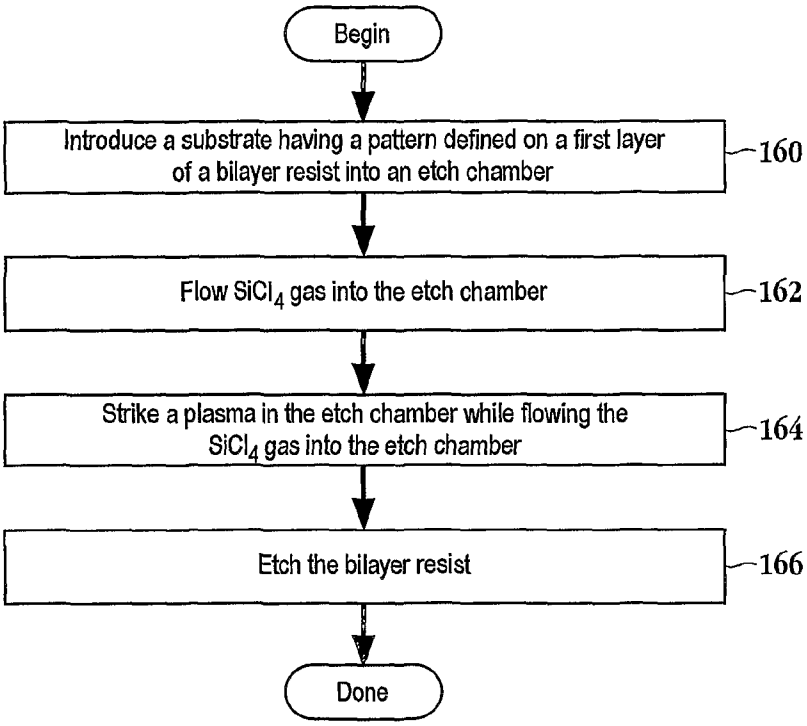
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[Continued on next page]

(54) Title: METHOD FOR BILAYER RESIST PLASMA ETCH



(57) Abstract: A method for etching a bilayer resist defined over a substrate in a plasma etch chamber is provided. The method initiates with introducing the substrate having a pattern defined on a first layer of the bilayer resist into the etch chamber. Then, $SiCl_4$ gas flows into the etch chamber. Next, a plasma is struck in the etch chamber while flowing the $SiCl_4$ gas. Then the bilayer resist is etched.

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